Abstracts

Recent Developments in Monolithic Integration of InGaAsP/InP Optoelectronic Devices

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Monolithically integrated optoelectronic circuits combine optical devices such as light sources (injection lasers and light emitting diodes) and optical detectors with solid-state semiconductor devices such as field effect transistors, bipolar transistors, and others on a single semiconductor crystal. Here we review some of the integrated circuits that have been realized and discuss the laser structures suited for integration with emphasis on the InGaAsP/InP material system. Some results of high frequency modulation and performance of integrated devices are discussed.

❑ Return to main document.